



650V/ 8A Silicon Carbide Power Schottky Barrier Diode

Features

- Rated to 650V at 8 Amps
- Zero reverse recovery current
- Zero forward recovery voltage
- Temperature independent switching behaviour
- High temperature operation
- High frequency operation

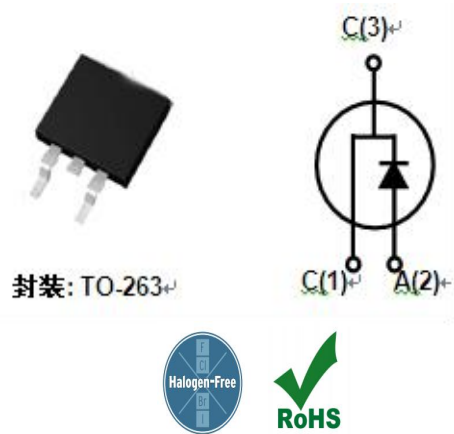
| Key Characteristics | | |
|-----------------------------------|------------|-----------|
| V_{RRM} | 650 | V |
| $I_F, T_c \leq 150^\circ\text{C}$ | 8 | A |
| Q_c | 30 | nC |

Benefits

- Unipolar rectifier
- Substantially reduced switching losses
- No thermal run-away with parallel devices
- Reduced heat sink requirements

Applications

- SMPS, e.g., CCM PFC;
- Motor drives, Solar application, UPS, Wind turbine, Rail traction, EV/HEV



| Part No. | Package Type | Marking |
|-----------|--------------|-----------|
| G3S06508D | TO-263 | G3S06508D |

Maximum Ratings

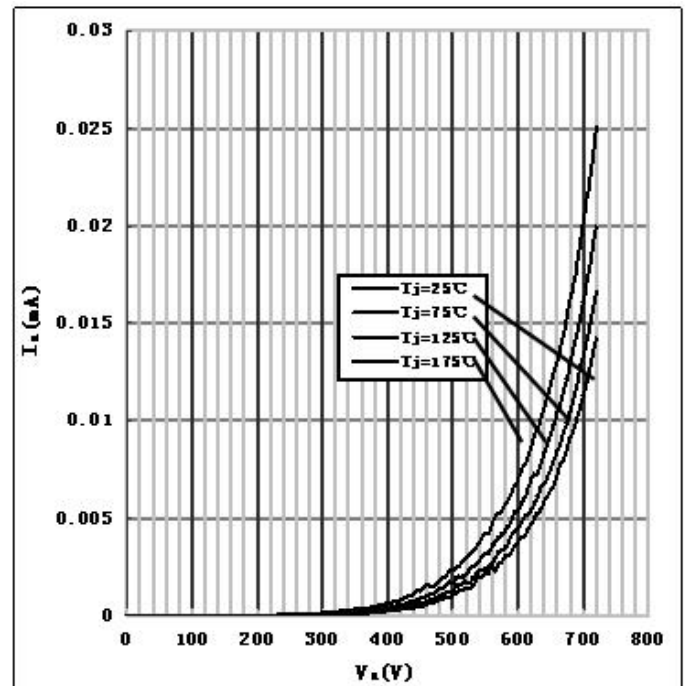
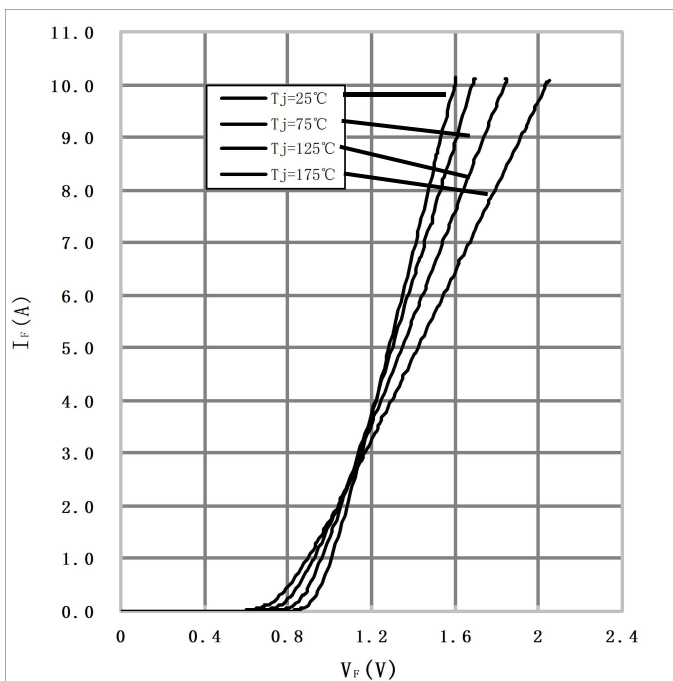
| Parameter | Symbol | Test Condition | Value | Unit |
|---|-----------|---|-----------------|--------|
| Repetitive Peak Reverse Voltage | V_{RRM} | | 650 | V |
| Surge Peak Reverse Voltage | V_{RSM} | | 650 | |
| DC Blocking Voltage | V_{DC} | | 650 | |
| Continuous Forward Current | I_F | $T_C=25^{\circ}C$ $T_C=135^{\circ}C$ $T_C=150^{\circ}C$ | 25.5 11 8 | A |
| Repetitive Peak Forward Surge Current | I_{FRM} | $T_C=25^{\circ}C$, $t_p=10ms$, Half Sine Wave, $D=0.3$ | 40 | A |
| Non-repetitive Peak Forward Surge Current | I_{FSM} | $T_C=25^{\circ}C$, $t_p=10ms$, Half Sine Wave | 105 | A |
| Power Dissipation | P_{TOT} | $T_C=25^{\circ}C$ | 114 | W |
| | | $T_C=110^{\circ}C$ | 49 | W |
| Operating Junction | T_j | | -55°C to 175°C | °C |
| Storage Temperature | T_{stg} | | -55°C to 175°C | °C |
| Mounting Torque | | M3 Screw | 1 | Nm |
| | | 6-32 Screw | 8.8 | lbf-in |

Thermal Characteristics

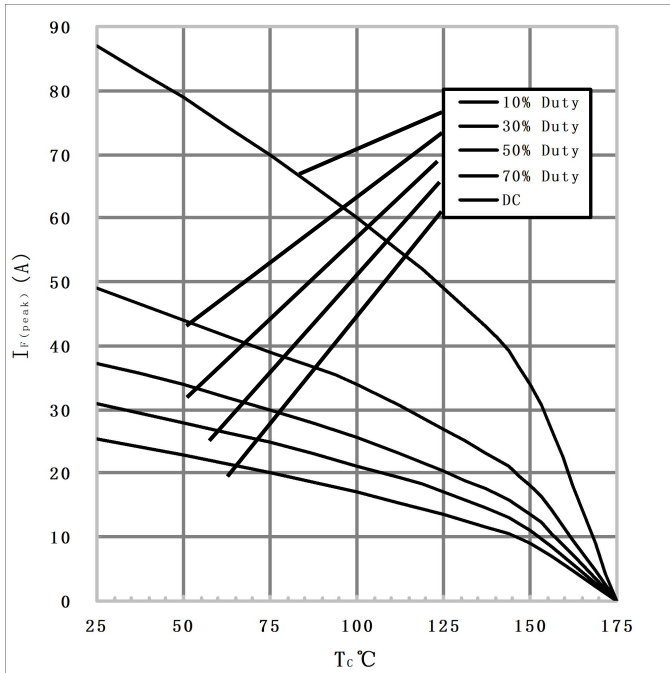
| Parameter | Symbol | Test Condition | Value | Unit |
|--|------------|----------------|-------|------|
| | | | Typ. | |
| Thermal resistance from junction to case | R_{thJC} | | 1.32 | °C/W |

Electrical Characteristics

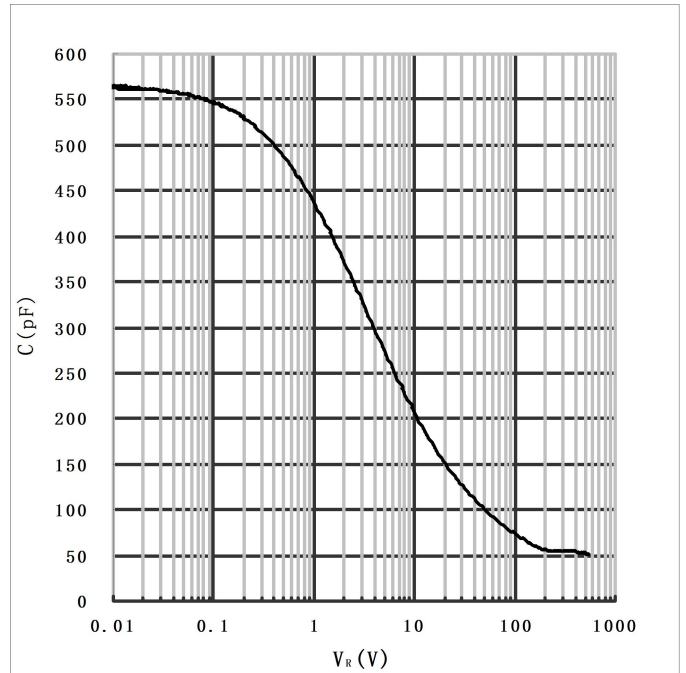
| Parameter | Symbol | Test Conditions | Numerical | | Unit |
|-------------------------|--------|--|-----------|------|---------|
| | | | Typ. | Max. | |
| Forward Voltage | V_F | $I_F=8A, T_j=25^\circ C$ | 1.37 | 1.7 | V |
| | | $I_F=8A, T_j=175^\circ C$ | 1.75 | 2.5 | |
| Reverse Current | I_R | $V_R=650V, T_j=25^\circ C$ | 10 | 50 | μA |
| | | $V_R=650V, T_j=175^\circ C$ | 20 | 100 | |
| Total Capacitive Charge | Q_C | $V_R=400V, T_j=150^\circ C$ $Q_C = \int_0^{V_R} C(V)dV$ | 30 | - | nC |
| Total Capacitance | C | $V_R=0V, T_j=25^\circ C, f=1MHz$ | 550 | 588 | pF |
| | | $V_R=200V, T_j=25^\circ C, f=1MHz$ | 56.5 | 57 | |
| | | $V_R=400V, T_j=25^\circ C, f=1MHz$ | 54 | 54.5 | |

Performance Graphs1) Forward IV characteristics as a function of T_j :2) Reverse IV characteristics as a function of T_j :

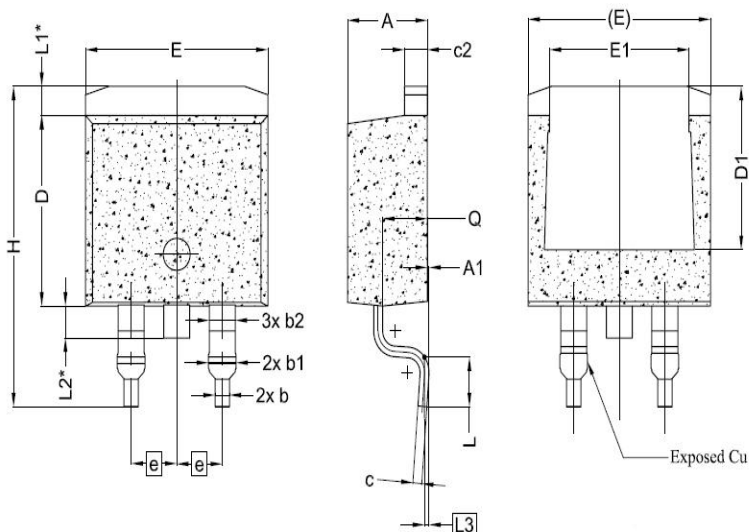
3) Current Derating



4) Capacitance vs. reverse voltage :



Package TO-263



| SYMBOL | DIMENSIONS | | |
|--------|------------|-------|-------|
| | MIN. | NOM. | MAX. |
| A | 4.24 | 4.44 | 4.64 |
| A1 | 0.00 | 0.10 | 0.25 |
| b | 0.70 | 0.80 | 0.90 |
| b1 | 1.20 | 1.55 | 1.75 |
| b2 | 1.20 | 1.45 | 1.70 |
| c | 0.40 | 0.50 | 0.60 |
| c2 | 1.15 | 1.27 | 1.40 |
| D | 8.82 | 8.92 | 9.02 |
| D1 | 6.86 | 7.65 | — |
| E | 9.96 | 10.16 | 10.36 |
| E1 | 6.89 | 7.77 | 7.89 |
| e | 2.54 BSC | | |
| H | 14.61 | 15.00 | 15.88 |
| L | 1.78 | 2.32 | 2.79 |
| L1 | 1.36 REF. | | |
| L2 | 1.50 REF. | | |
| L3 | 0.25 BSC | | |
| Q | 2.30 | 2.48 | 2.70 |

Note: The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC(RoHS2). RoHS Certification and other certifications can be obtained from GPT sales representatives or GPT website: <http://globalpowertech.cn/English/index.asp>

More product datasheets and company information can be found in:

<http://globalpowertech.cn/English/index.asp>

